

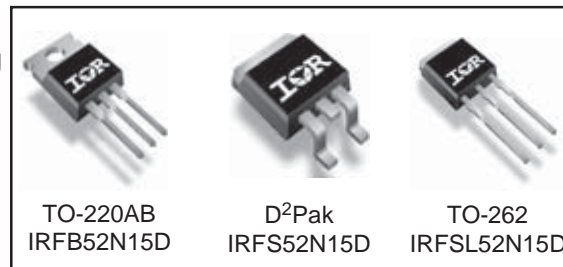
**Applications**

- High frequency DC-DC converters

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on) max</sub></b>	<b>I<sub>D</sub></b>
<b>150V</b>	<b>0.032Ω</b>	<b>60A</b>

**Benefits**

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>OSS</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	60	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	43	
I <sub>DM</sub>	Pulsed Drain Current ①	240	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation ②	3.8	W
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	320	
	Linear Derating Factor	2.1	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Mounting torque, 6-32 or M3 screw ④	10 lbf•in (1.1N•m)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	0.47	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat, Greased Surface ⑤	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient ⑥	—	62	
R <sub>θJA</sub>	Junction-to-Ambient ⑦	—	40	

Notes ① through ⑦ are on page 11

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## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.16	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.032	$\Omega$	$V_{GS} = 10V, I_D = 36A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 120V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

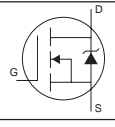
## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	19	—	—	S	$V_{DS} = 50V, I_D = 36A$
$Q_g$	Total Gate Charge	—	60	89	nC	$I_D = 36A$
$Q_{gs}$	Gate-to-Source Charge	—	18	27		$V_{DS} = 75V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	28	42		$V_{GS} = 10V$ , ④
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 75V$
$t_r$	Rise Time	—	47	—		$I_D = 36A$
$t_{d(off)}$	Turn-Off Delay Time	—	28	—		$R_G = 2.5\Omega$
$t_f$	Fall Time	—	25	—		$V_{GS} = 10V$ ④
$C_{iss}$	Input Capacitance	—	2770	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	590	—		$V_{DS} = 25V$
$C_{riss}$	Reverse Transfer Capacitance	—	110	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	3940	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	260	—		$V_{GS} = 0V, V_{DS} = 120V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	550	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 120V$ ⑤

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②⑥	—	470	mJ
$I_{AR}$	Avalanche Current①	—	36	A
$E_{AR}$	Repetitive Avalanche Energy①	—	32	mJ

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	60	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①⑥	—	—	240		
$V_{SD}$	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 36A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	140	210	nS	$T_J = 25^\circ\text{C}, I_F = 36A$
$Q_{rr}$	Reverse Recovery Charge	—	780	1170	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

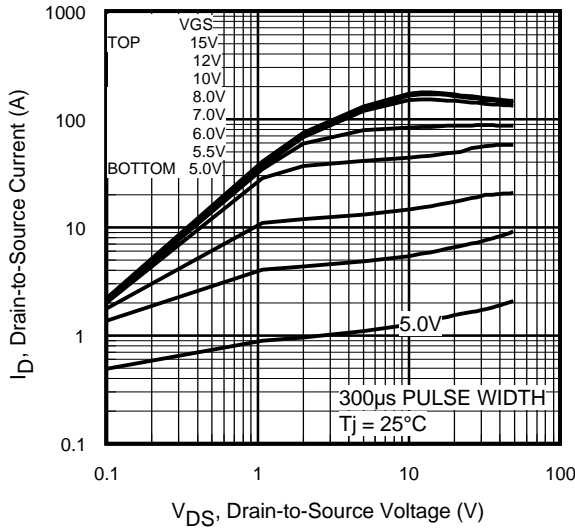


Fig 1. Typical Output Characteristics

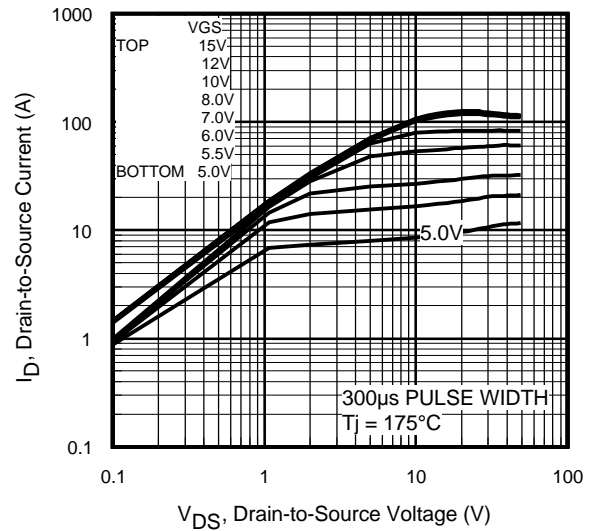


Fig 2. Typical Output Characteristics

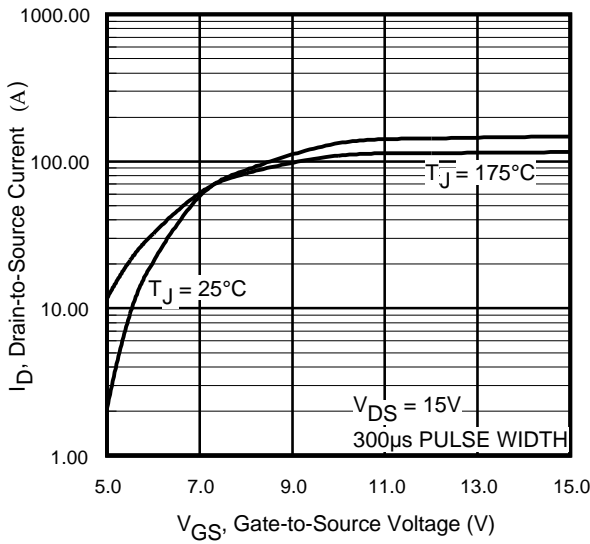


Fig 3. Typical Transfer Characteristics

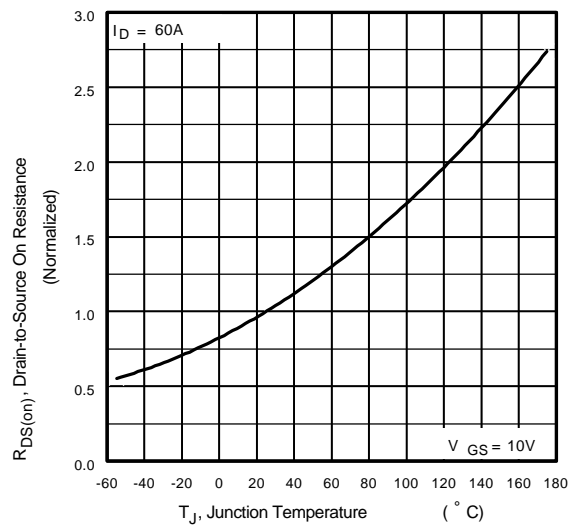
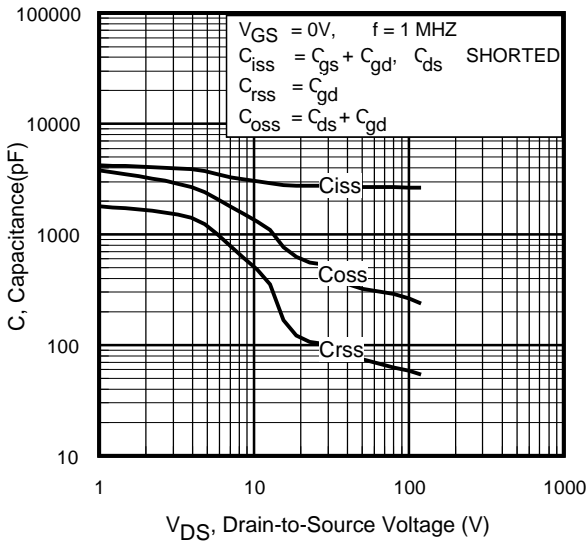


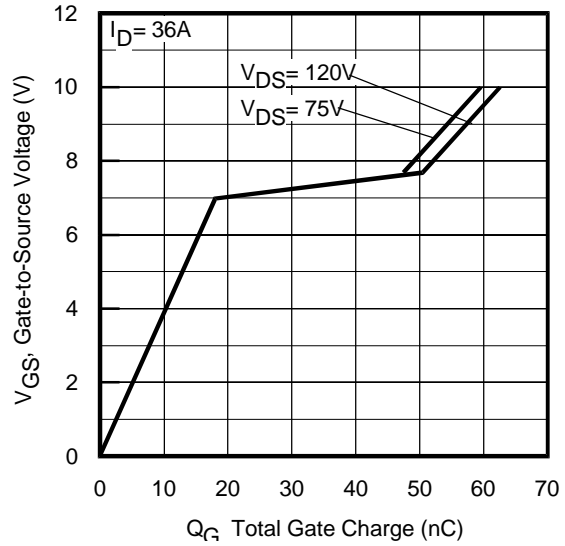
Fig 4. Normalized On-Resistance Vs. Temperature

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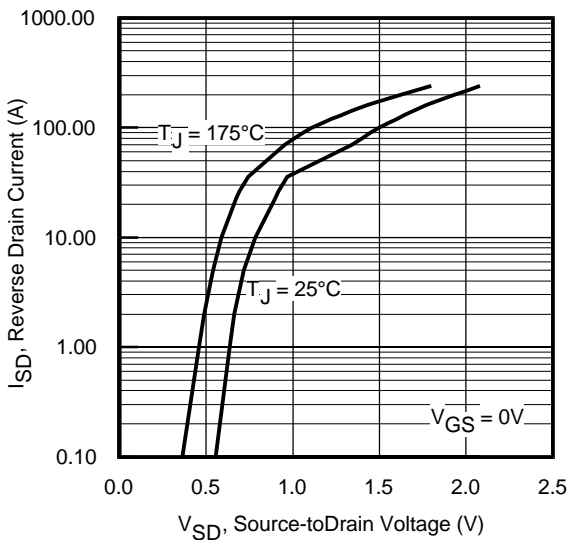
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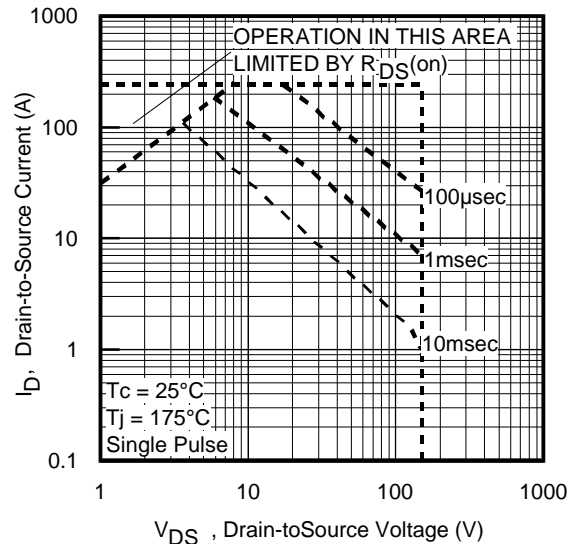
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

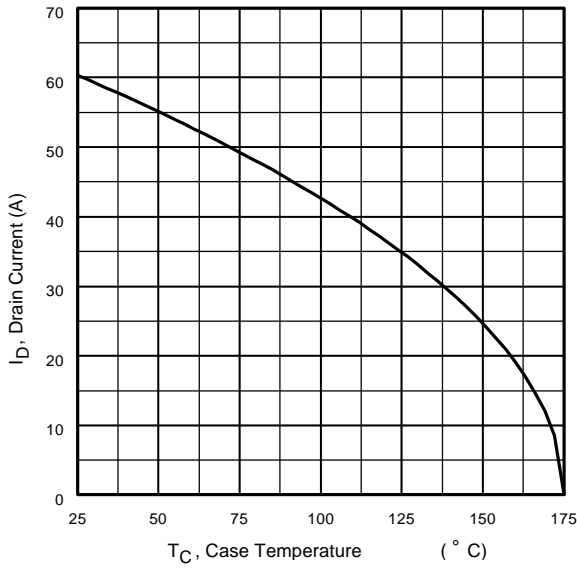


Fig 9. Maximum Drain Current Vs. Case Temperature

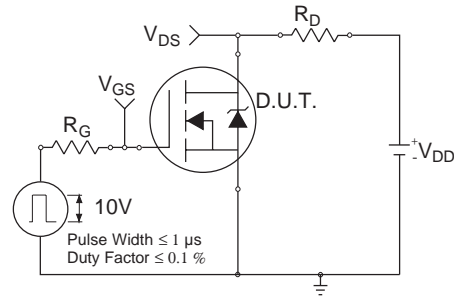


Fig 10a. Switching Time Test Circuit

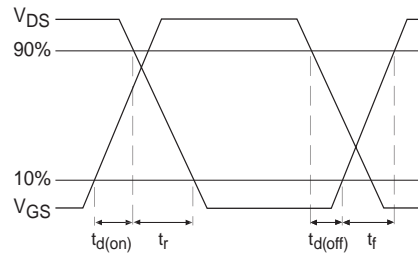


Fig 10b. Switching Time Waveforms

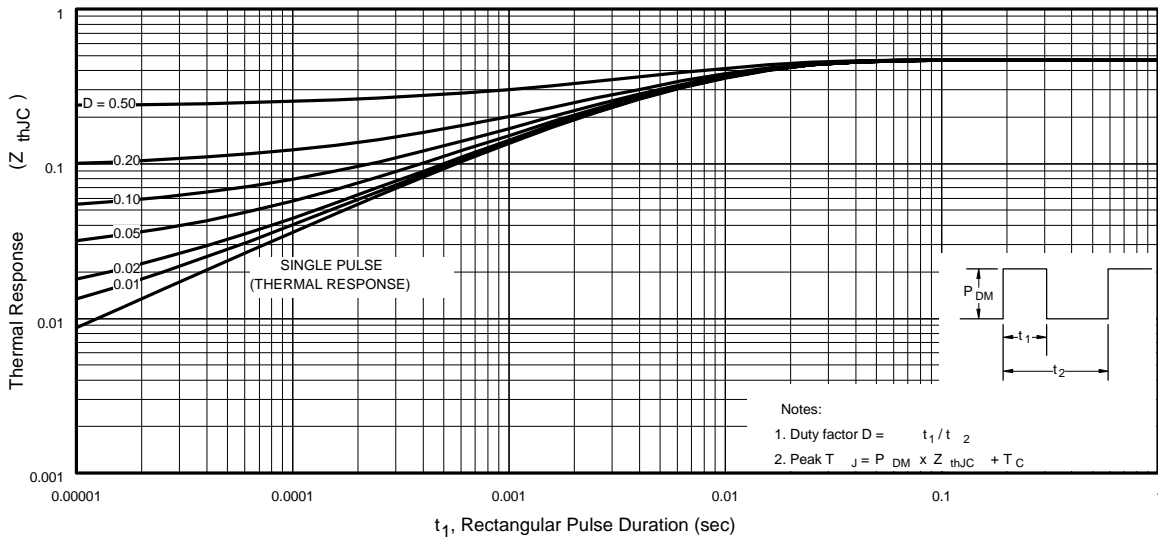
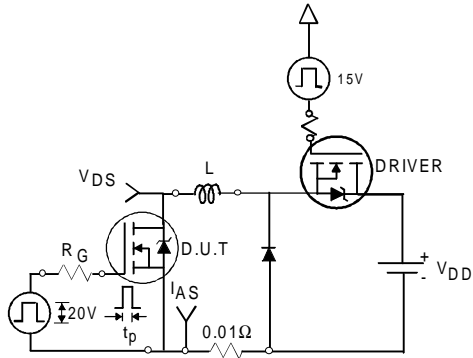


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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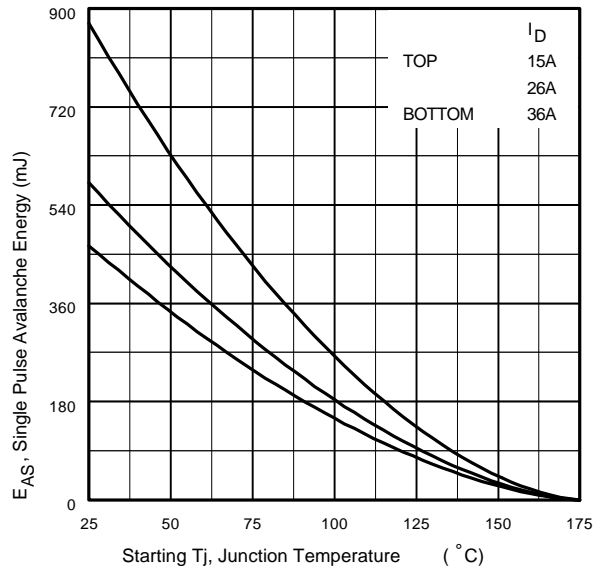
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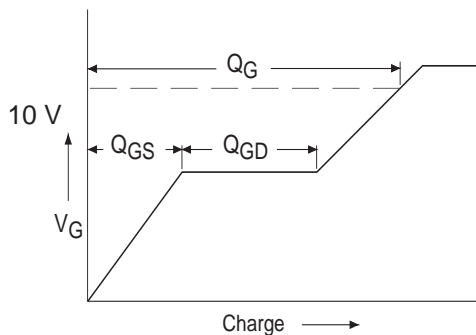
**Fig 12a.** Unclamped Inductive Test Circuit



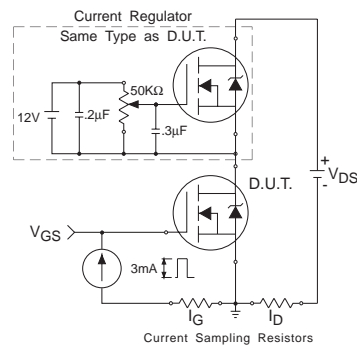
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

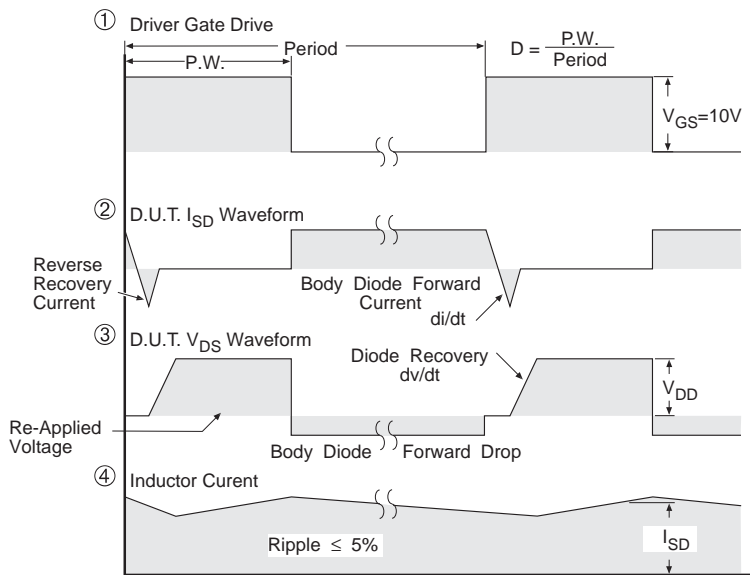
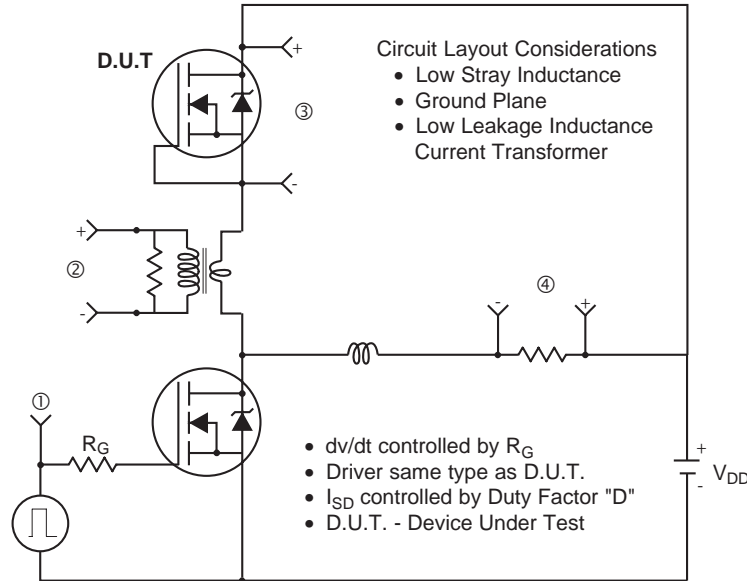


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

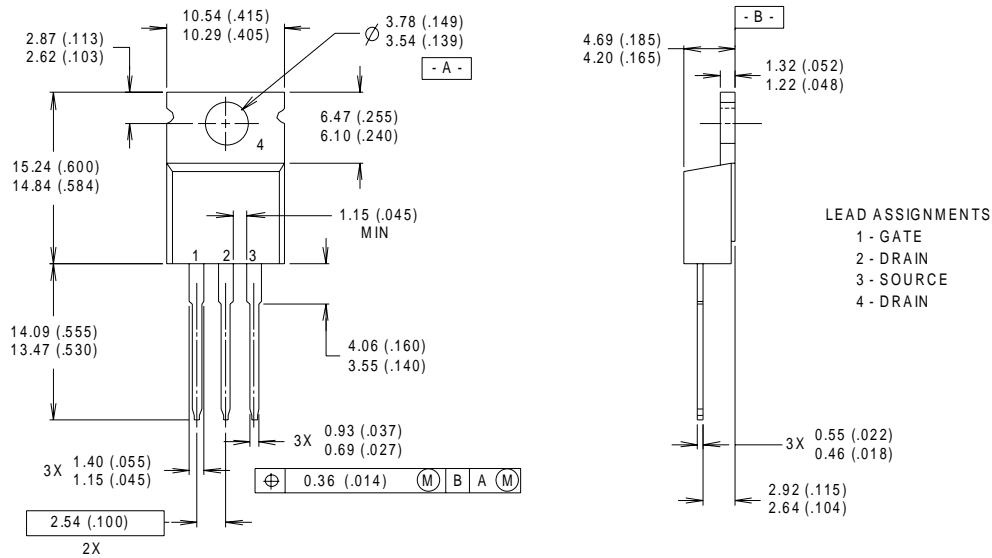
**Fig 14.** For N-Channel HEXFET® Power MOSFETs

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## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



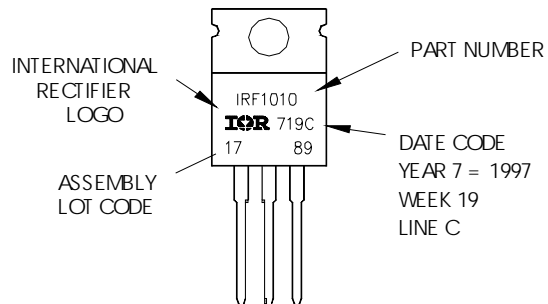
### NOTES:

1 DIMENSIONING & TOLERANCING PER ANS Y14.5M, 1982.  
2 CONTROLLING DIMENSION : INCH

3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.  
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

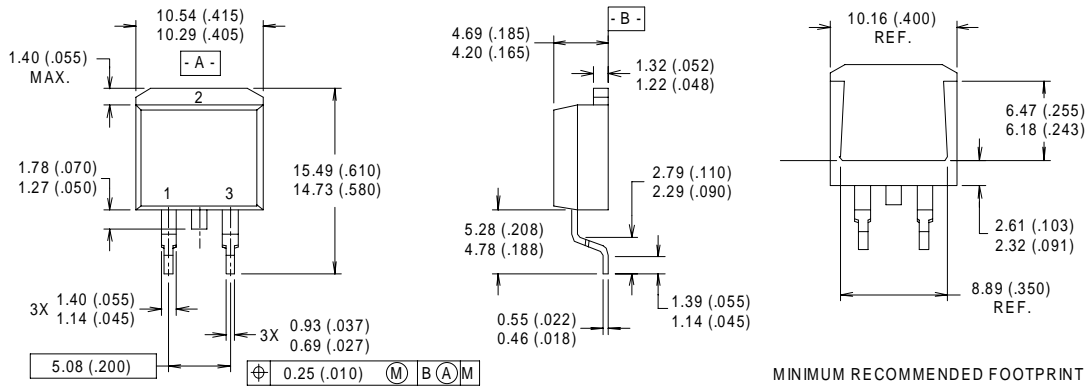
## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
LOT CODE 1789  
ASSEMBLED ON WW19, 1997  
IN THE ASSEMBLY LINE "C"





## D<sup>2</sup>Pak Package Outline



**NOTES:**

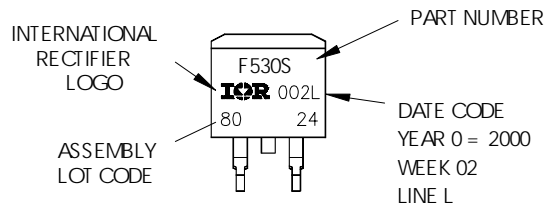
- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

**LEAD ASSIGNMENTS**

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

## D<sup>2</sup>Pak Part Marking Information

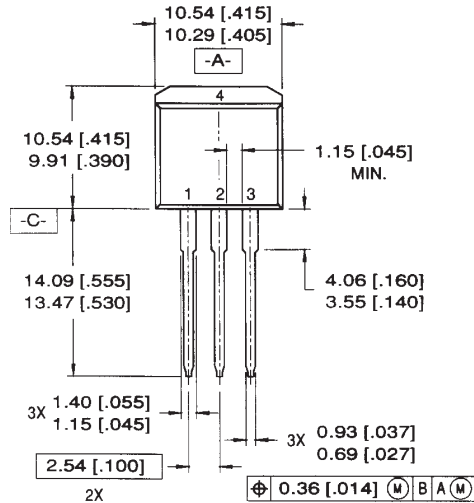
EXAMPLE: THIS IS AN IRF530S WITH  
 LOT CODE 8024  
 ASSEMBLED ON WW02, 2000  
 IN THE ASSEMBLY LINE "L"



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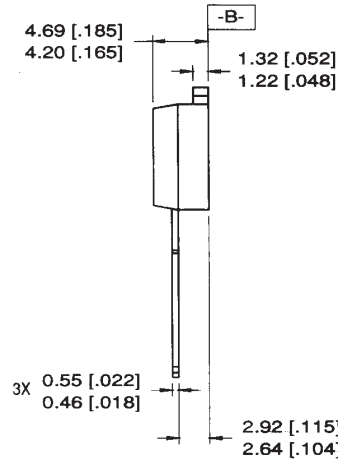
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## TO-262 Package Outline



### LEAD ASSIGNMENTS

1 = GATE      3 = SOURCE  
2 = DRAIN    4 = DRAIN

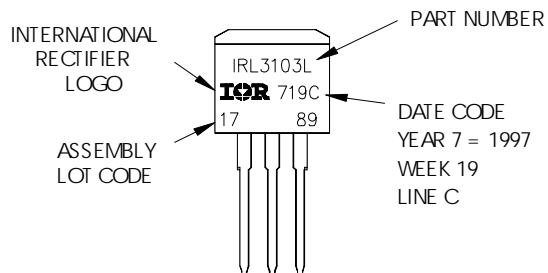


### NOTES:

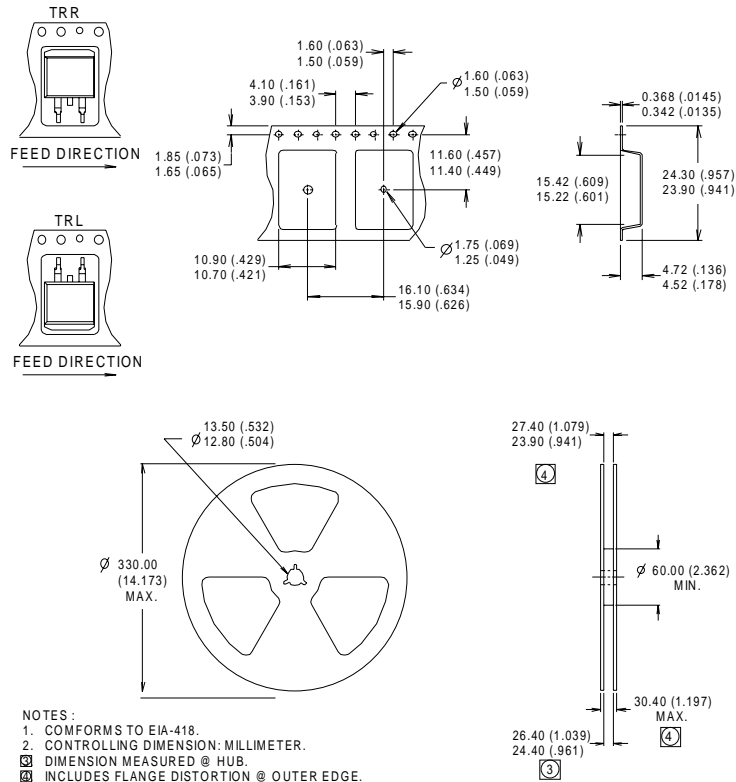
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON VW 19, 1997  
IN THE ASSEMBLY LINE "C"



## D<sup>2</sup>Pak Tape & Reel Information



NOTES:  
 1. CONFORMS TO EIA-418.  
 2. CONTROLLING DIMENSION: MILLIMETER.  
 3. DIMENSION MEASURED @ HUB.  
 4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.72\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 36\text{A}$ .
- ③  $I_{SD} \leq 36\text{A}$ ,  $di/dt \leq 400\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥ This is only applied to TO-220AB package.
- ⑦ This is applied to D<sup>2</sup>Pak, when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

**TO-220 package is not recommended for Surface Mount Application.**

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Automotive [Q101] (IRFB52N15D),  
 & Industrial (IRFS/SL52N15D) market.  
 Qualification Standards can be found on IR's Web site.

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**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
 TAC Fax: (310) 252-7903

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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>